AMENDMENTS TO THE SPECIFICATION

Please replace the third full paragraph on page 1 with the following amended paragraph:

In ULSI wiring, attendant upon the requirements of an increase in capacity ~~of ULSI~~ and a decrease in cost of manufacture, it is desired to decrease ~~in~~ the size of the wiring structure and simplify the manufacturing process. ~~From~~ To achieve these points, ~~as~~ the mainstream fabrication techniques for ULSI wiring structures, at present, is a dual damascene processes ~~are mainstream~~ (hereinafter referred to as prior art 1).

Please replace the last full paragraph on page 1 with the following amended paragraph:

In ULSI wiring according to the prior art 1, ~~in case that~~when a wiring layer is made of Cu (copper), Cu constituting the wiring layer diffuses into an insulating interlayer ~~so that it~~and may bring about bad insulation. Therefore, it is indispensable to interpose a diffusion prevention layer between the wiring layer and the insulating interlayer and thereby prevent Cu from diffusing into the insulating interlayer.

Please replace the last full paragraph on page 2 with the following amended paragraph:

~~Besides, i~~In the above-described process, many steps are required ~~till~~ to complete the fabrication of the wiring layer. ~~In addition~~The above process also requires, two processes that are different in phase, such as the dry processes of sputtering and CVD ~~as dry processes,~~ and the

wet process of electroplating ~~as a wet process, must be performed~~. Therefore, the above process is both complicated and ~~it is~~ disadvantageous in cost.

Please replace the second full paragraph on page 3 with the following amended paragraph:

It is an object of the present invention to provide a method of manufacturing ULSI wiring~~, which~~ that makes it possible to ~~perform all the formations of~~form the diffusion prevention layer~~, and further~~ the wiring layer, and the capping layer through wet processes, and in which the diffusion prevention layer is good in adhesion[[,]]and ~~further~~ the wiring ~~layer and the~~and capping layers~~, can be~~are formed through a simple process.

Please replace the second full paragraph on page 14 with the following amended paragraph:

In a process of manufacturing ULSI wiring before the diffusion prevention layer is formed on the organic silane layer and after the organic silane layer is deposited on the first insulation layer, the organic silane layer is subjected to heat-decomposition by heating ~~of the process~~ at a temperature~~, for example~~of 300°C or more, for example, ~~in the process~~ to form an adhesion layer containing at least one of silicon (Si) and carbon (C).

Please replace the paragraph bridging pages 14-15 with the following amended paragraph:

Furthermore, in a process of manufacturing ULSI wiring after the diffusion prevention layer is formed on the organic silane layer, the adhesion layer is heat-decomposed at ~~the~~ a temperature~~, for example~~ of 300°C or more, for example, ~~in the process from the organic silane layer~~ to form silicon (Si) and carbon (C), and ~~which~~ Si and C are further diffused into the diffusion prevention layer by heating to form a diffusion prevention layer containing at least one of Si and C.